

INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)
YOR919990509US3
(13171AB)

Application Number
~~Unassigned~~
10/827064

Applicant(s)
Cyril Cabral, Jr., et al.

Filing Date
~~Herewith~~ 4/19/04

Group Art Unit
~~Unassigned~~ 2813

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EL		5,510,295	4/23/96	Cabral, Jr., et al.	—	—	
		5,608,226	3/4/97	Yamada, et al.	—	—	
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FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EL	M. Lawrence, et al., "Growth of Epitaxial CoSi ₂ on (100) Si, "Appl. Phys. Lett., Vol. 58, No. 12, pp. 1308-1310 (1991).
EL	Wolf, Silicon Processing for the VLSI Era, Vol. 2-Process Intergration, Lattice Press: Sunset Beach CA, 1990, pp. 144-151.
EL	C. Cabral, et al., "In-Situ X-Ray Diffractin and Resistivity Analysis of CoSi ₂ Phase Formation With and Without a Ti Interlayer at Rapid Thermal Annealing Rates, "Mat. Res. Soc. Symp. Proc., Vol. 375, pp. 253-258 (1995).

EXAMINER *Em Kin*

DATE CONSIDERED 12/11/2004

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EK		4,965,645 A	10/1990	Solomon.	—	—	
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							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EK		Huang, et al. "Impact of Ge implantation on the electrical characteristics of TiSi ₂ p+n shallow junctions with an a-Si (or poly-Si) buffer layer" in IEEE Transactions on Electron Devices, 44(4), April 1997, pp. 601-606.
EK		Prabhakaran, et al. "Diffusion mediated chemical reaction in Co/Ge/Si(100) forming Ge/CoSi ₂ /Si(100)" in Applied Physics Letters 68(9), 26 February 1996, pp. 1241-1243.

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